

BAT85/86(For Glass Seal)

Chip Information

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|--|------------------------------|
| Chip Size | 0.39 x 0.39mm |
| Pad Size | 0.30 x 0.30mm |
| Chip Quantity | 72690 pcs/wafer |
| Scribe Line Width | 50um |
| Passivation | PSG |
| Wafer Size | 5 inch |
| Top Metallization | Ag Bump 30um(For Glass Seal) |
| Chip Thickness/Back Metal : See below "Ordering Information" | |

MAXIMUM RATINGS

| Parameter | Symbol | Limit | Unit | Note |
|---|---------|-------------|------|-----------------------------|
| Repetitive Peak Reverse Voltage | VRRM | 50 | V | |
| Non-Repetitive Peak Reverse Voltage | VRSM | | V | |
| Maximum DC Blocking Voltage | VR | 50 | V | |
| Average Forward Rectified Current | IF(AV) | 200 | mA | |
| Peak Forward Surge Current | IFSM | 5 | A | 8.3ms Single Half Sine-Wave |
| Storage and Operating Temperature Range | Tj,TSTG | -65 to +125 | degC | |

ELECTRICAL CHARACTERISTICS

| Parameter | Symbol | Spec Limit | Test Spec | Typical | Unit | Test Condition |
|----------------------------|---------|------------|-----------|---------|------|--------------------|
| Maximum Forward Voltage | VF1 | 0.800 | 0.790 | 0.600 | V | IF=100mA Ta=25degC |
| | VF2 | 0.500 | 0.490 | 0.415 | V | IF=30mA Ta=25degC |
| | VF3 | 0.400 | 0.390 | 0.340 | V | IF=10mA Ta=25degC |
| | VF4 | 0.320 | 0.315 | 0.260 | V | IF=1mA Ta=25degC |
| | VF5 | 0.240 | 0.235 | 0.200 | V | IF=100uA Ta=25degC |
| Maximum DC Reverse Current | IR1 | 2 | 1 | 0.3 | uA | VR=25V Ta=25degC |
| | IR2 | 5 | 3 | 0.4 | uA | VR=40V Ta=25degC |
| | IR3 | | | | uA | |
| | IR4 | | | | uA | |
| Reverse Breakdown Voltage | BV1 | 50 | 55 | 70 | V | IR=100uA |
| | BV2 | 50 | 55 | 70 | V | IR=500uA |
| | deltaBV | 2.5 | 2 | | V | BV2-BV1 |
| Junction Capacitance | Cj | | | 7 | pF | V=1V,f=1MHz |
| Reverse Recovery Time | trr | | | | nS | |

Ordering Information

| Chip Type | Chip Thickness | Back Metal |
|-----------|----------------|--------------------------|
| YFS17A | 200 +/- 20um | Ti-Ni-Ag(For Glass Seal) |

Note:
Designed For BAT85/86